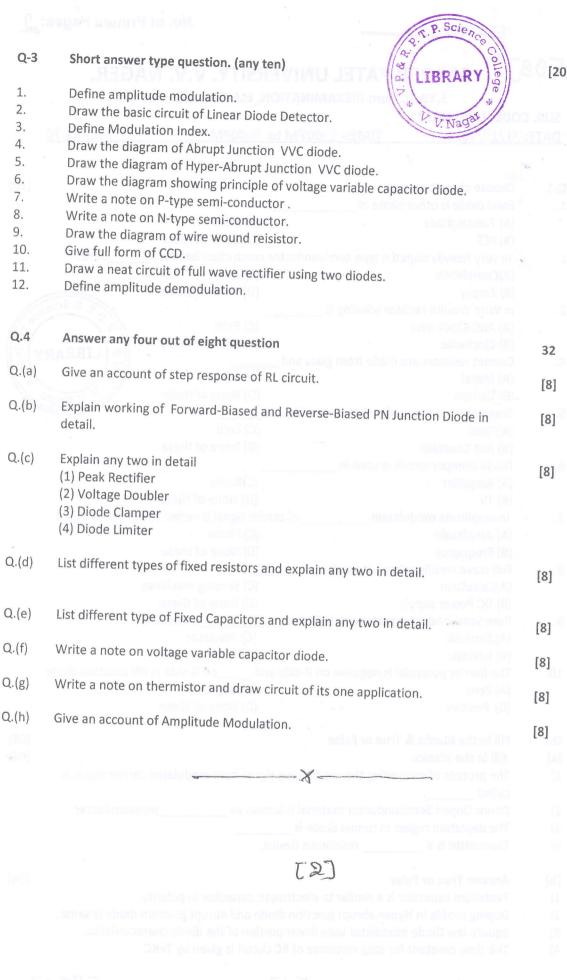
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598	S.YB.Sc. S		RSITY. V.V. NA	
	CODE:-US03CELE21	TIME:- 2:00 PM to	0.4:00PM	MARKS-70
		. WC diode	agram of Aerupt Junction	A. The Design of the Color of t
Q-1	Choose correct answe	Michon The diade.		[10
Q-1 1	Esaki diode is other na			ona a atholid
1	(A) Tunnel diode		(C) BJT	
	(B) FET		(D) None of these	
2.			r conduction band is	filled.
<u>~</u> .		in type bermeenducter		11 Drate a neat
	(B) Empty		(D) None of these	lands and bell
3.	In Wire Wound resisto	r winding is	(2) 110110 01 11000	R.P. Science
0.	(A) Anti-Clock wise		(C) Both	
	(B) Clockwise		(D) None of these	LIBRARY College
4.	Cermet resistors are m			di LIBRARY
	(A) Metal	L streuk,	(C) Gold	*
	(B) Carbon		(D) None of these	L' L'Nagai
5.	There are two types of	resistors variable and	ing of Forward-Staged b	. IVag
	(A)Fixed		(C) Zero	
	(B) Not Constant		(D) None of these	
6.	Diode clamper circuit i	s used in	NO ID DETAIL	
	(A) Amplifier		(C)Radio	
	(B) TV		(D) None of these	
7.	In amplitude modulat	ionof car	rier signal is varied as pe	r audio signal.
	(A) Amplitude		(C) Phase	
	(B) Frequency		(D) None of these	
8.	Full wave rectifier circ	uit is used in	sypes of thest resistons a	
	(A)Calculator		(C) Sensing machines	
	(B) DC Power supply		(D) None of these	
9.	Pure Semiconductor m	naterial is called as	material.	191500 (81
	(A) Extrinsic		(C) Insulator	
	(B) Intrinsic		(D) None of these	
10.			ndon N-side in PN	Junction diode
	(A) Zero		., .	
	(B) Positive		(D) None of these	
0.2	Fill in the Disales 0 To	in an Palas		(00)
Q.2	Fill in the Blanks & Tru	le or Faise		(08)
[a]	Fill in the blanks. (04 The process of recovering the modulating signal from modulated carrier signal is			
1)		ring the modulating si	ghai from modulated car	rier signal is
21	called	du sha u usaha utal ta lua.		
2)	Donor Doped Semiconductor material is known assemiconductor.			conductor.
3)	The depletion region in tunnel diode is Thermistor is a resistance device.			
4)	mermistor is a	resistance device	a	
[b]	Answer True or False			(04)
[b] 1)				
2)	Tantalium capacitor is a similar to electrolytic capacitor in polarity. Doping profile in Hyper-abrupt junction diode and abrupt junction diode is same.			
3)	Square law Diode modulator uses linear portion of the diode characteristics.			
4)			ircuit is given by T=RC	

[1]

[P.T.O.]



[20]